

BFR340F

Low profile silicon NPN RF bipolar transistor



Product description

The BFR340F is a low noise device based on Si that is part of Infineon's established third generation RF bipolar transistor family. Its low current and high breakdown voltage characteristics make the device suitable for oscillators applications for frequencies as high as 3.5 GHz. It remains cost competitive without compromising on ease of use.



Feature list

- Minimum noise figure $NF_{min} = 1$ dB at 1.9 GHz, 1.5 V, 1 mA
- High gain $G_{ms} = 16.5$ dB at 1.8 GHz, 3 V, 5 mA
- $OIP_3 = 13$ dBm at 1.8 GHz, 3 V, 5 mA

Product validation

Qualified for industrial applications according to the relevant tests of JEDEC47/20/22.

Potential applications

- Low noise amplifiers (LNAs) for FM and AM radio
- LNAs for sub-1 GHz ISM band applications

Device information

Table 1 Part information

Product name / Ordering code	Package	Pin configuration			Marking	Pieces / Reel
BFR340F / BFR340FH6327XTSA1	TSFP-3-1	1 = B	2 = E	3 = C	FAs	3000

Attention: ESD (Electrostatic discharge) sensitive device, observe handling precautions

Table of contents

	Product description	1
	Feature list	1
	Product validation	1
	Potential applications	1
	Device information	1
	Table of contents	2
1	Absolute maximum ratings	3
2	Thermal characteristics	4
3	Electrical characteristics	5
3.1	DC characteristics	5
3.2	General AC characteristics	5
3.3	Frequency dependent AC characteristics	6
3.4	Characteristic AC diagrams	8
4	Package information TSFP-3-1	14
	Revision history	15
	Disclaimer	16

Absolute maximum ratings

1 Absolute maximum ratings

Table 2 Absolute maximum ratings at $T_A = 25\text{ °C}$ (unless otherwise specified)

Parameter	Symbol	Values		Unit	Note or test condition
		Min.	Max.		
Collector emitter voltage	V_{CEO}	–	6	V	Open base
Collector emitter voltage	V_{CES}		15		E-B short circuited
Collector base voltage	V_{CBO}		15		Open emitter
Emitter base voltage	V_{EBO}		2		Open collector
Base current	I_B		2	mA	–
Collector current	I_C		20		
Total power dissipation ¹⁾	P_{tot}		75	mW	$T_S \leq 110\text{ °C}$
Junction temperature	T_J		150	°C	–
Storage temperature	T_{Stg}	-55			

Attention: *Stresses above the max. values listed here may cause permanent damage to the device. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Exceeding only one of these values may cause irreversible damage to the integrated circuit.*

¹ T_S is the soldering point temperature. T_S is measured on the emitter lead at the soldering point of the PCB.

Thermal characteristics

2 Thermal characteristics

Table 3 Thermal resistance

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Junction - soldering point	R_{thJS}	–	530	–	K/W	–

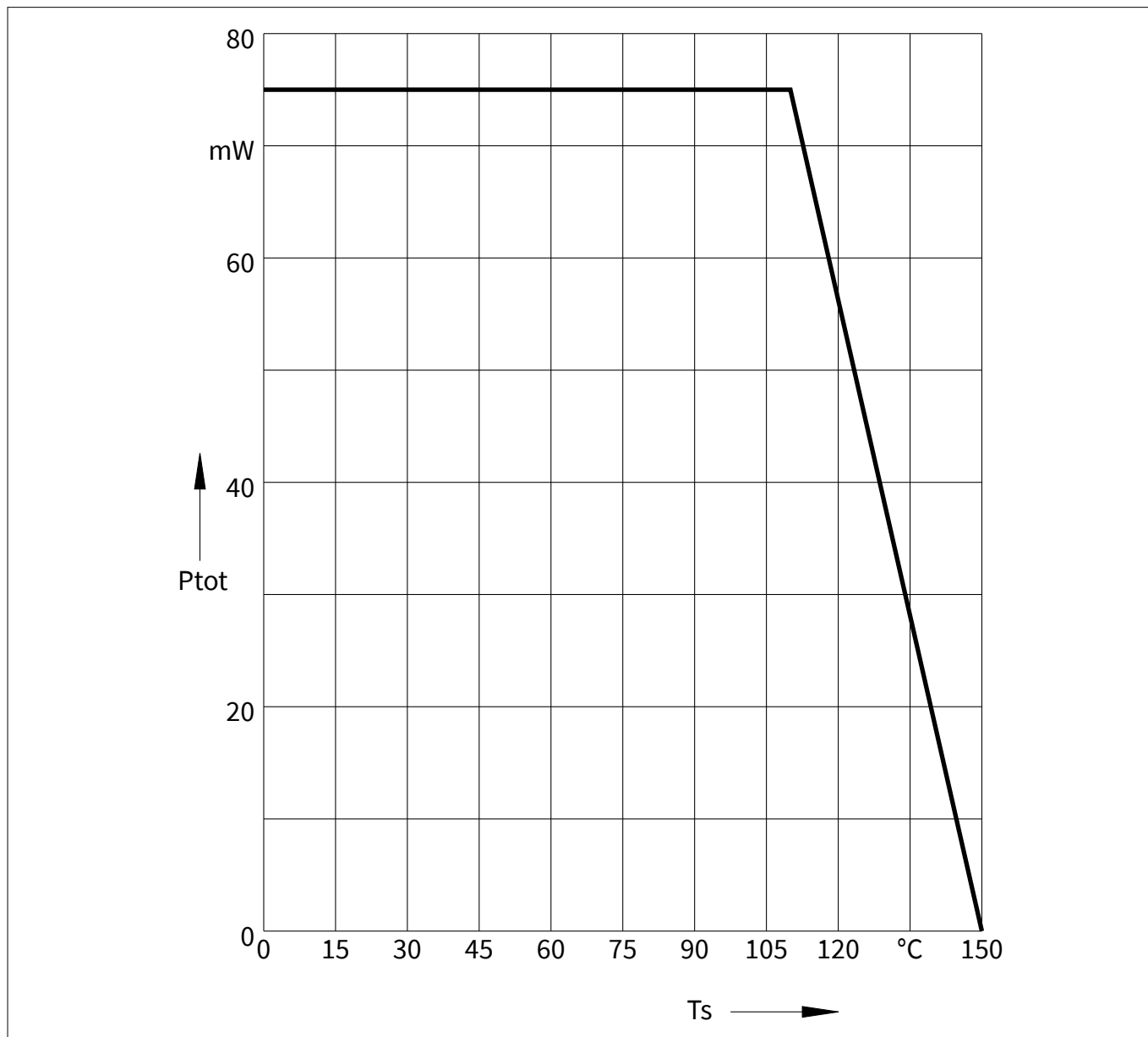


Figure 1 Total power dissipation $P_{tot} = f(T_s)$

Electrical characteristics

3 Electrical characteristics

3.1 DC characteristics

Table 4 DC characteristics at $T_A = 25\text{ °C}$ (unless otherwise specified)

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Collector emitter breakdown voltage	$V_{(BR)CEO}$	6	9	–	V	$I_C = 1\text{ mA}$, $I_B = 0$, open base
Collector emitter leakage current	I_{CES}	–	1	30 ²⁾	nA	$V_{CE} = 4\text{ V}$, $V_{BE} = 0$, E-B short circuited
			2	50 ²⁾		$V_{CE} = 10\text{ V}$, $V_{BE} = 0$, $T_A = 85\text{ °C}$, E-B short circuited
Collector base leakage current	I_{CBO}		1	30 ²⁾		$V_{CB} = 4\text{ V}$, $I_E = 0$, open emitter
Emitter base leakage current	I_{EBO}		1	500 ²⁾		$V_{EB} = 1\text{ V}$, $I_C = 0$, open collector
DC current gain	h_{FE}	90	120	160		$V_{CE} = 3\text{ V}$, $I_C = 5\text{ mA}$, pulse measured

3.2 General AC characteristics

Table 5 General AC characteristics at $T_A = 25\text{ °C}$

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Transition frequency	f_T	11	14	–	GHz	$V_{CE} = 3\text{ V}$, $I_C = 6\text{ mA}$, $f = 1\text{ GHz}$
Collector base capacitance	C_{CB}	–	0.21	0.4	pF	$V_{CB} = 5\text{ V}$, $V_{BE} = 0$, $f = 1\text{ MHz}$, emitter grounded
Collector emitter capacitance	C_{CE}		0.17	–		$V_{CE} = 5\text{ V}$, $V_{BE} = 0$, $f = 1\text{ MHz}$, base grounded
Emitter base capacitance	C_{EB}		0.11	–		$V_{EB} = 0.5\text{ V}$, $V_{CB} = 0$, $f = 1\text{ MHz}$, collector grounded

² Maximum values not limited by the device but by the short cycle time of the 100% test.

Electrical characteristics

3.3 Frequency dependent AC characteristics

Measurement setup is a test fixture with Bias-T's in a 50 Ω system, $T_A = 25^\circ\text{C}$.

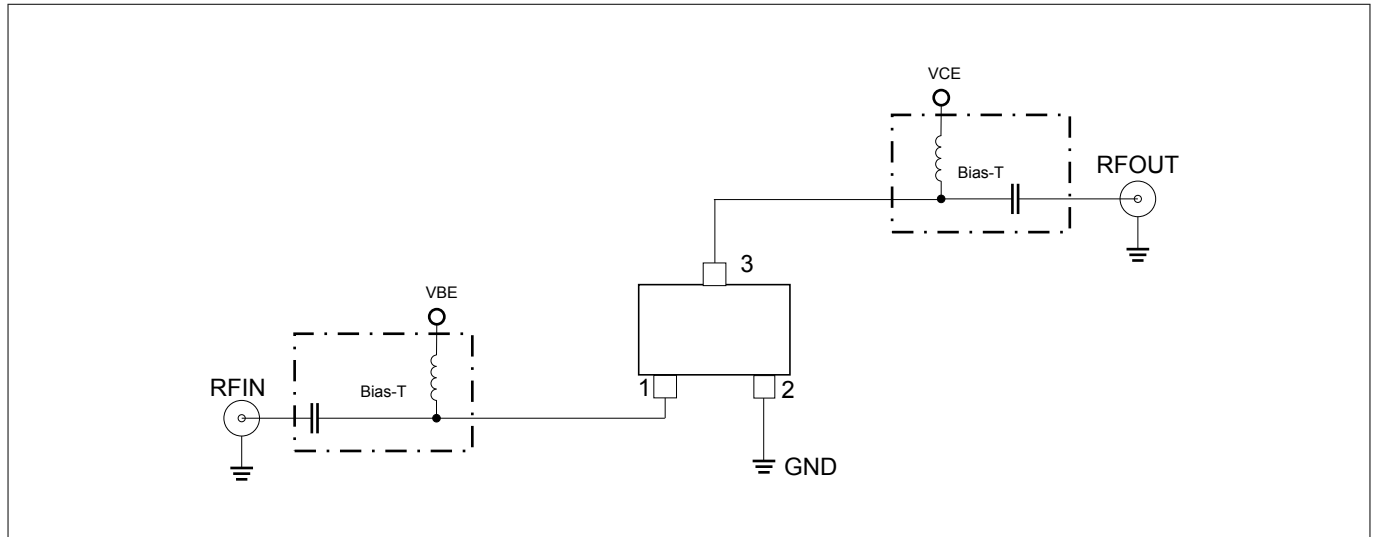


Figure 2 Testing circuit

Table 6 AC characteristics, $f = 100\text{ MHz}$

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain		–		–	dB	$I_C = 3\text{ mA}$, $V_{CE} = 1.5\text{ V}$
• Maximum power gain	G_{ms}		28			
• Transducer gain	$ S_{21} ^2$		19			
Noise figure						
• Minimum noise figure	NF_{min}		0.9			$I_C = 3\text{ mA}$, $V_{CE} = 1.5\text{ V}$
Linearity						
• 3rd order intercept point at output	OIP_3		14		dBm	$I_C = 5\text{ mA}$, $V_{CE} = 3\text{ V}$, $Z_S = Z_L = 50\ \Omega$
• 1 dB gain compression point at output	OP_{1dB}		-3			

Table 7 AC characteristics, $V_{CE} = 3\text{ V}$, $f = 1.8\text{ GHz}$

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain		–		–	dB	$I_C = 5\text{ mA}$
• Maximum power gain	G_{ms}		16.5			
• Transducer gain	$ S_{21} ^2$		14			
Linearity						
• 3rd order intercept point at output	OIP_3		13		dBm	$I_C = 5\text{ mA}$, $Z_S = Z_L = 50\ \Omega$
• 1 dB gain compression point at output	OP_{1dB}		-1			

Electrical characteristics

Table 8 AC characteristics, $f = 1.9$ GHz

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain	G_{ms} $ S_{21} ^2$	–	16.3	–	dB	$I_C = 5$ mA, $V_{CE} = 3$ V
• Maximum power gain			13.4			
Noise figure	NF_{min}		1			$I_C = 1$ mA, $V_{CE} = 1.5$ V
• Minimum noise figure						

Table 9 AC characteristics, $f = 2.4$ GHz

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain	G_{ms} $ S_{21} ^2$	–	14.9	–	dB	$I_C = 5$ mA, $V_{CE} = 3$ V
• Maximum power gain			11.6			
Noise figure	NF_{min}		1.2			$I_C = 1$ mA, $V_{CE} = 1.5$ V
• Minimum noise figure						

Table 10 AC characteristics, $V_{CE} = 3$ V, $f = 3$ GHz

Parameter	Symbol	Values			Unit	Note or test condition
		Min.	Typ.	Max.		
Power gain	G_{ms} $ S_{21} ^2$	–	13	–	dB	$I_C = 5$ mA
• Maximum power gain			10			
• Transducer gain						

Note: $G_{ms} = |S_{21}|^2 / S_{12} I$ for $k < 1$; $G_{ma} = |S_{21}|^2 / S_{12} I (k - (k^2 - 1)^{1/2})$ for $k > 1$. In order to get the NF_{min} values stated in this chapter, the test fixture losses have been subtracted from all measured results. OIP_3 value depends on termination of all intermodulation frequency components. Termination used for this measurement is 50 Ω from 0.1 MHz to 6 GHz.

Electrical characteristics

3.4 Characteristic AC diagrams

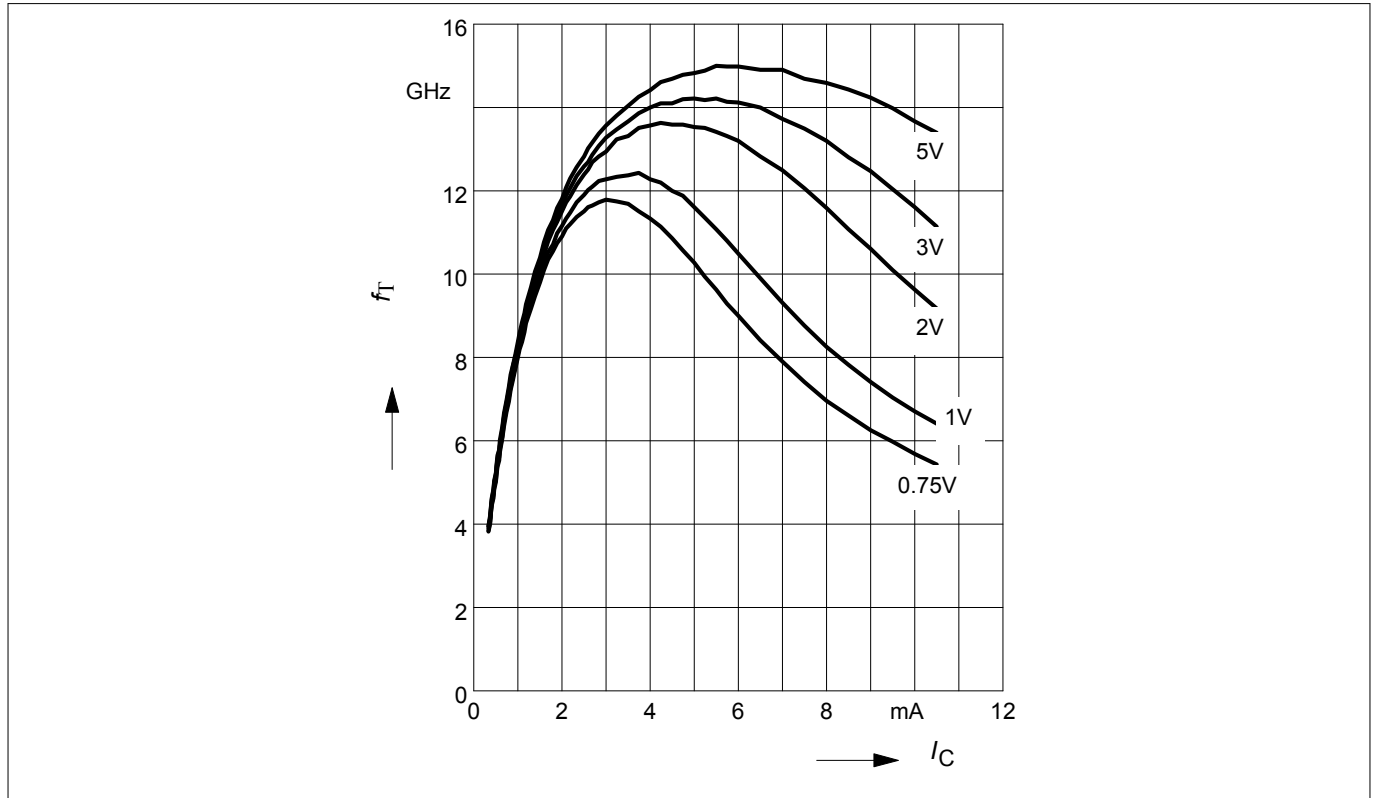


Figure 3 Transition frequency $f_T = f(I_C)$, $f = 1 \text{ GHz}$, $V_{CE} = \text{parameter}$

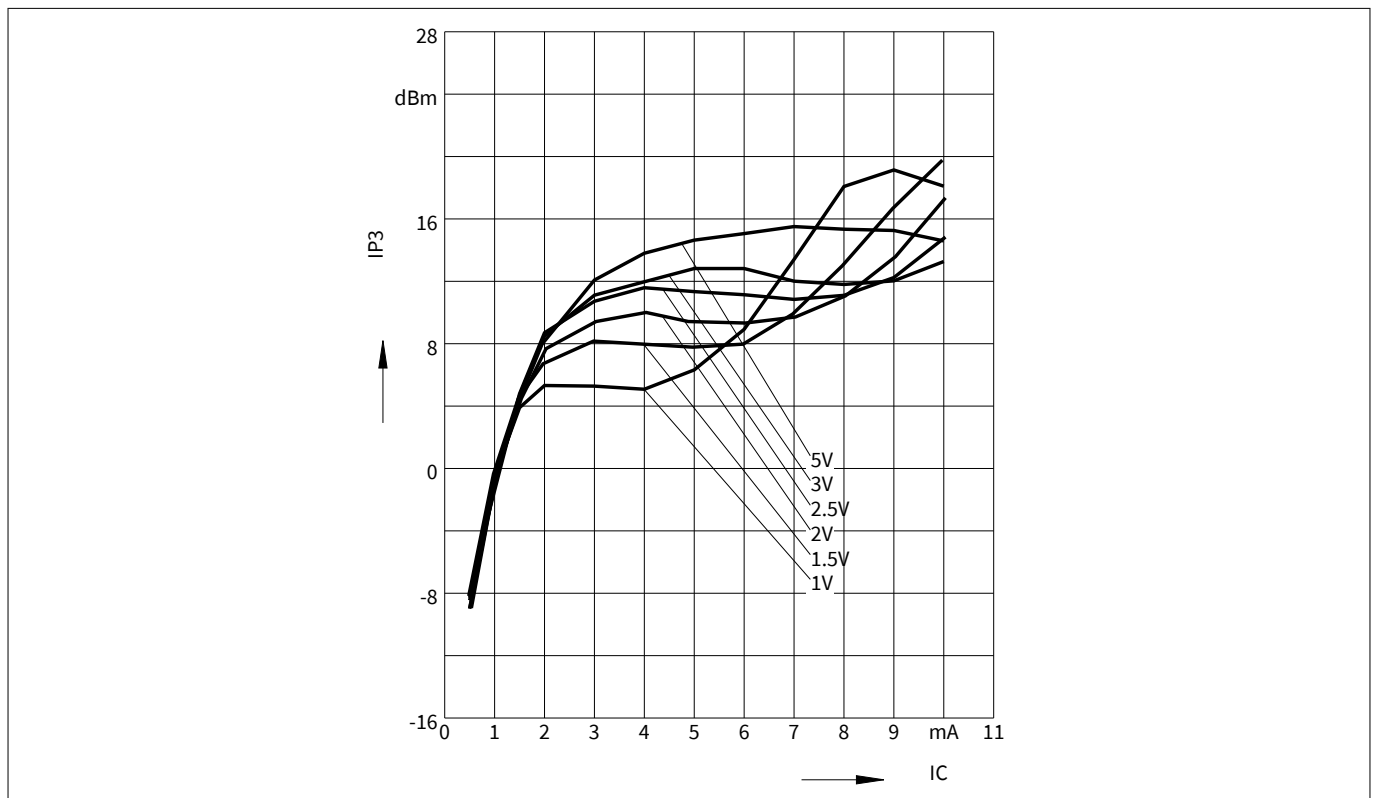


Figure 4 3rd order intercept point $OIP_3 = f(I_C)$, $Z_S = Z_L = 50 \Omega$, $f = 1.9 \text{ GHz}$, $V_{CE} = \text{parameter}$

Electrical characteristics

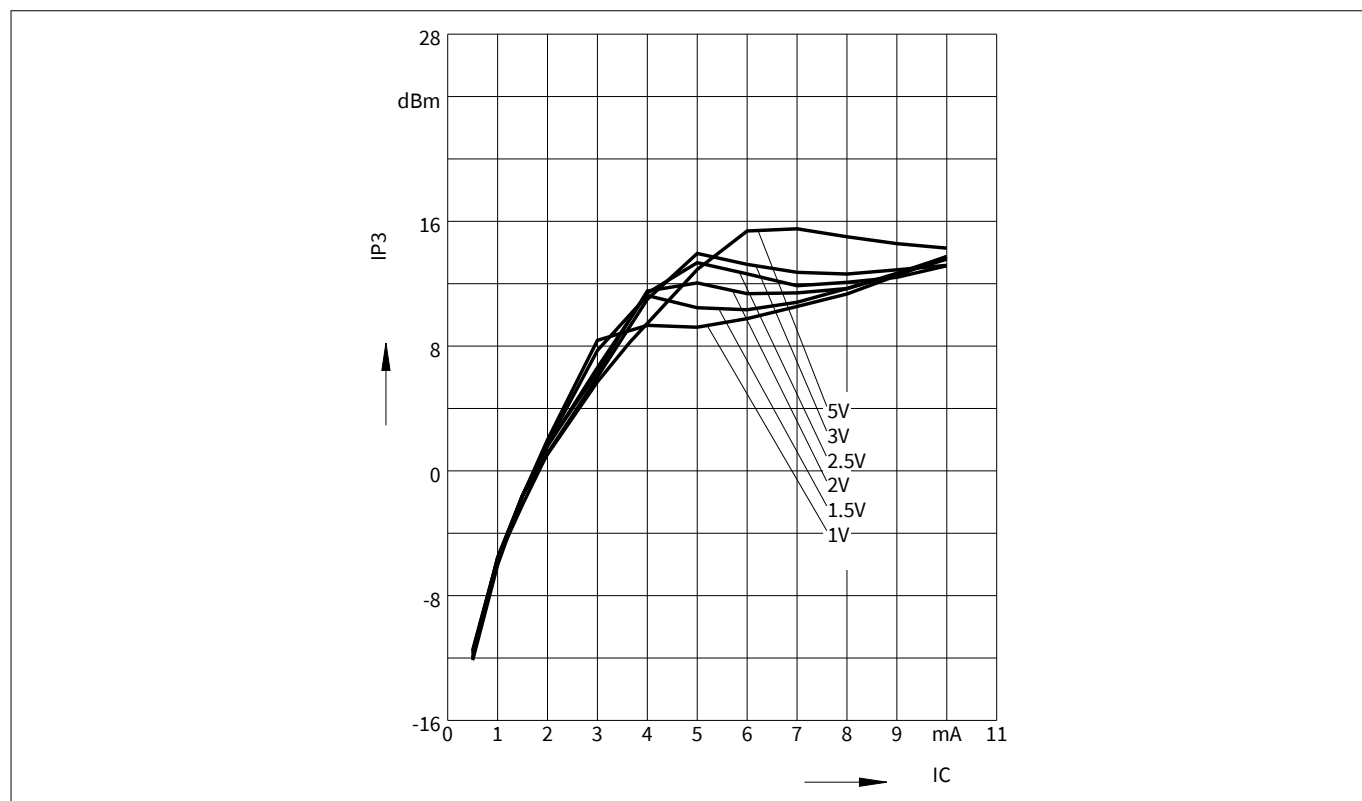


Figure 5 3rd order intercept point $OIP_3 = f(I_C, V_{CE})$, $Z_S = Z_L = 50 \Omega$, $f = 100 \text{ MHz}$

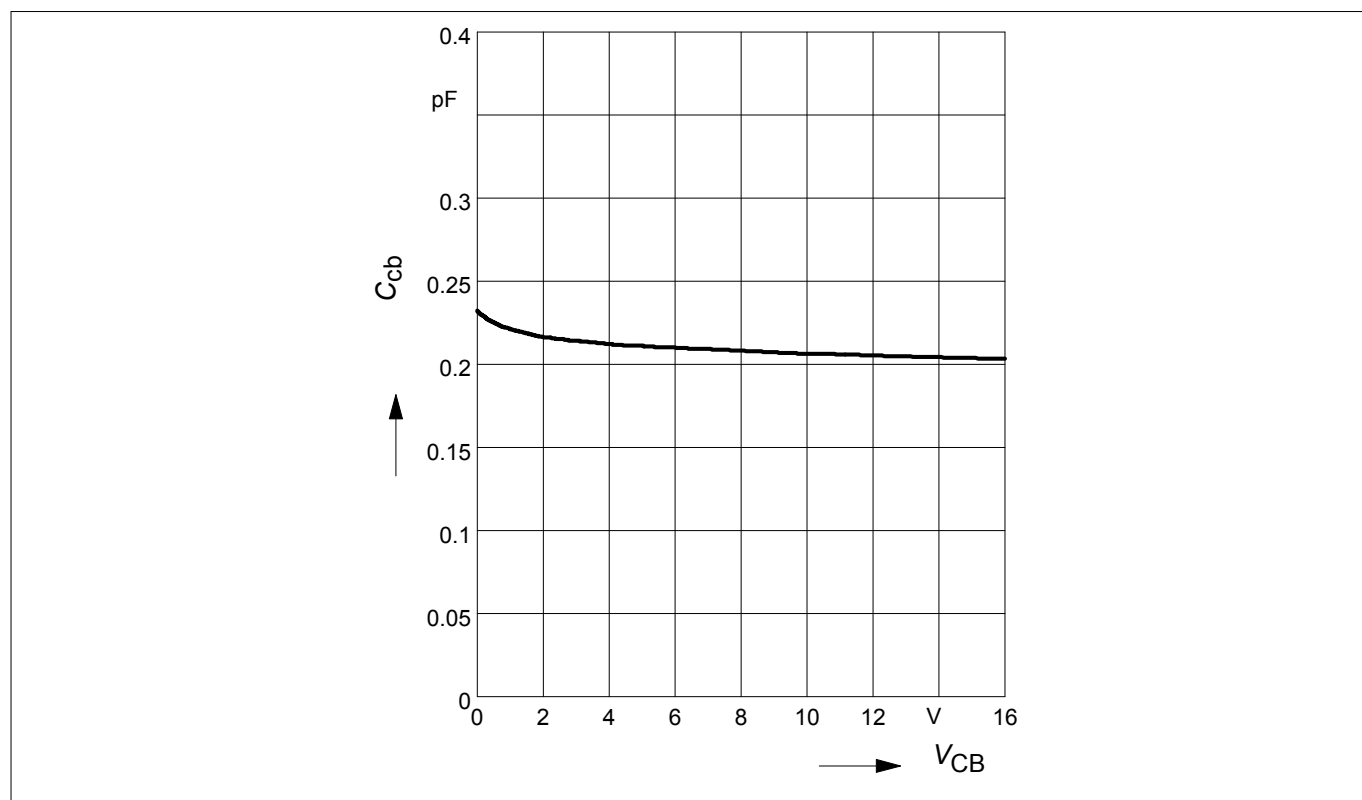


Figure 6 Collector base capacitance $C_{CB} = f(V_{CB})$, $f = 1 \text{ MHz}$

Electrical characteristics

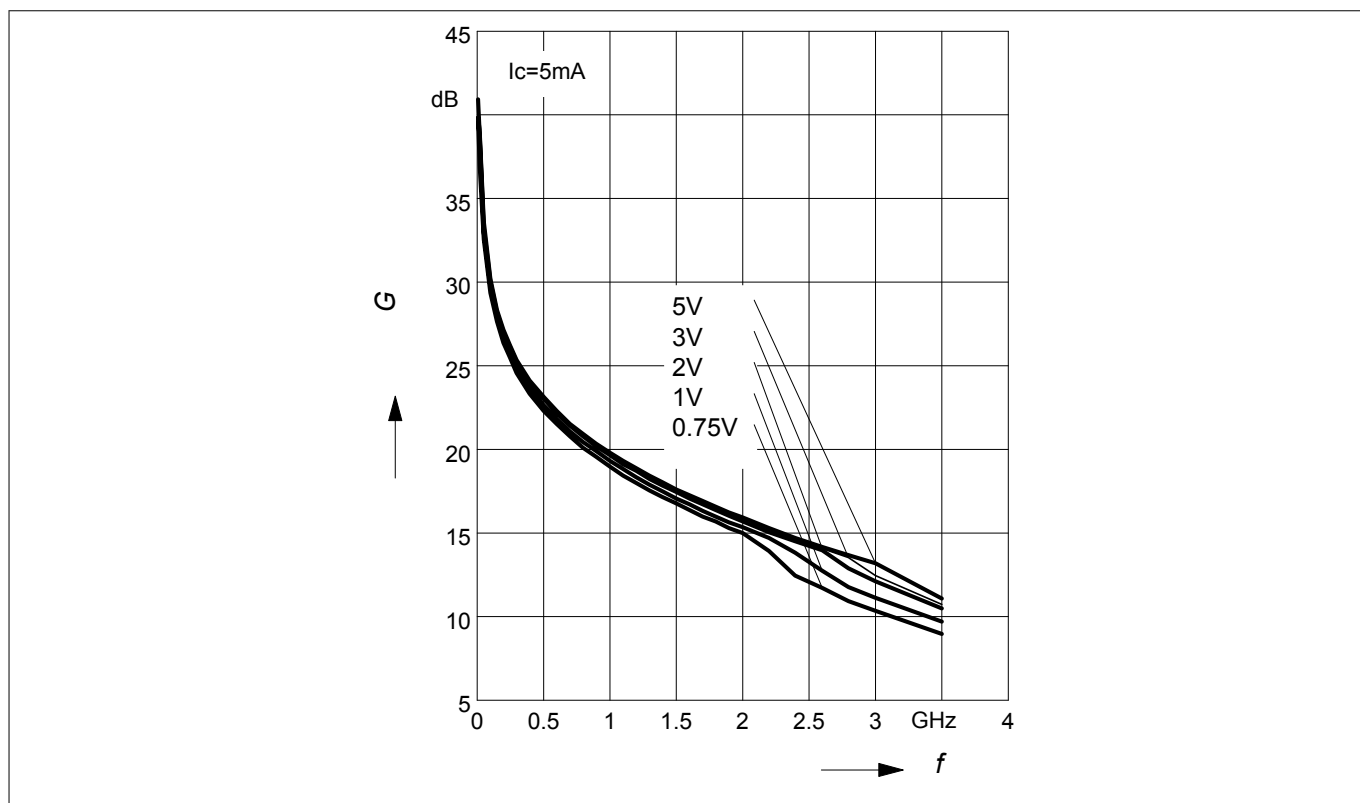


Figure 7 Gain G_{ma} , $G_{ms} = f(f)$, $I_C = 5\text{ mA}$, $V_{CE} = \text{parameter}$

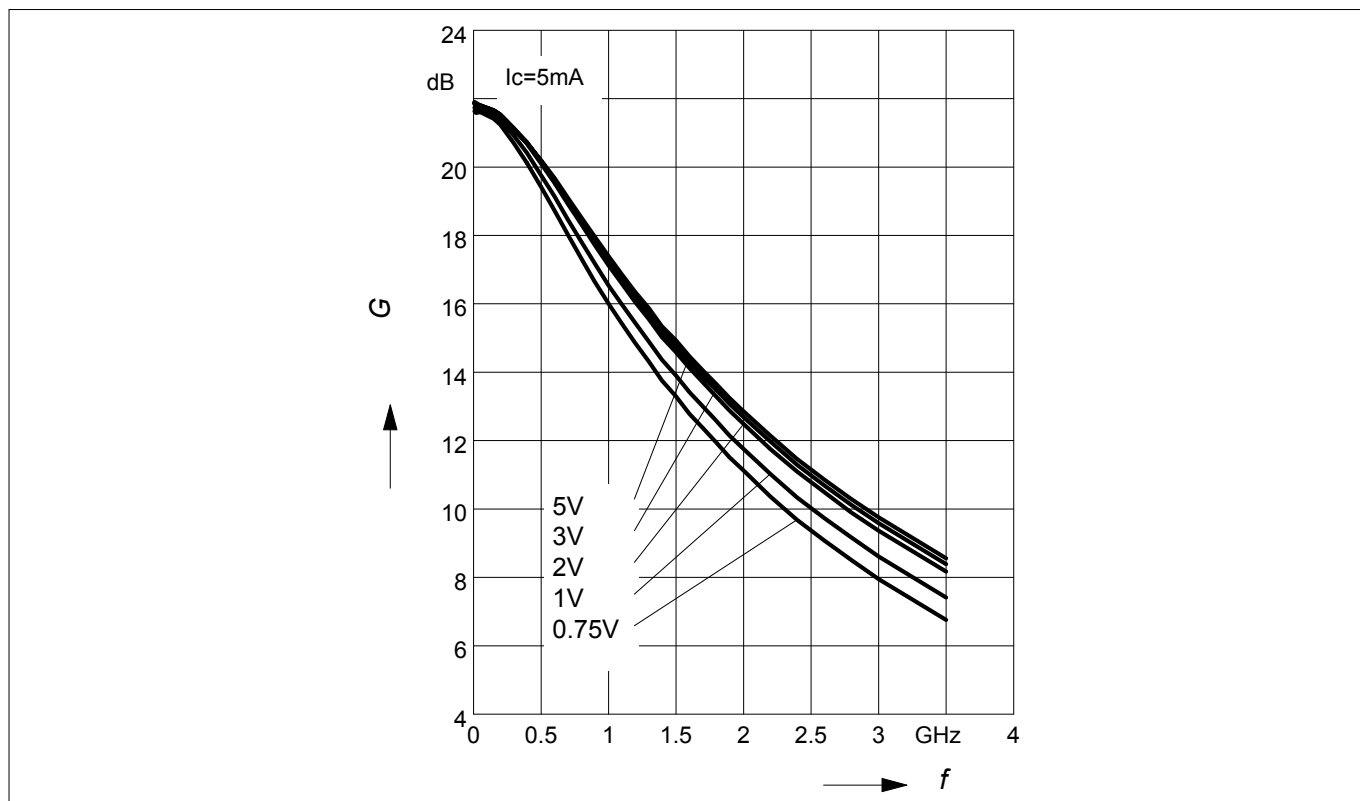


Figure 8 Transducer gain $IS_{21}I^2 = f(f)$, $I_C = 5\text{ mA}$, $V_{CE} = \text{parameter}$

Electrical characteristics

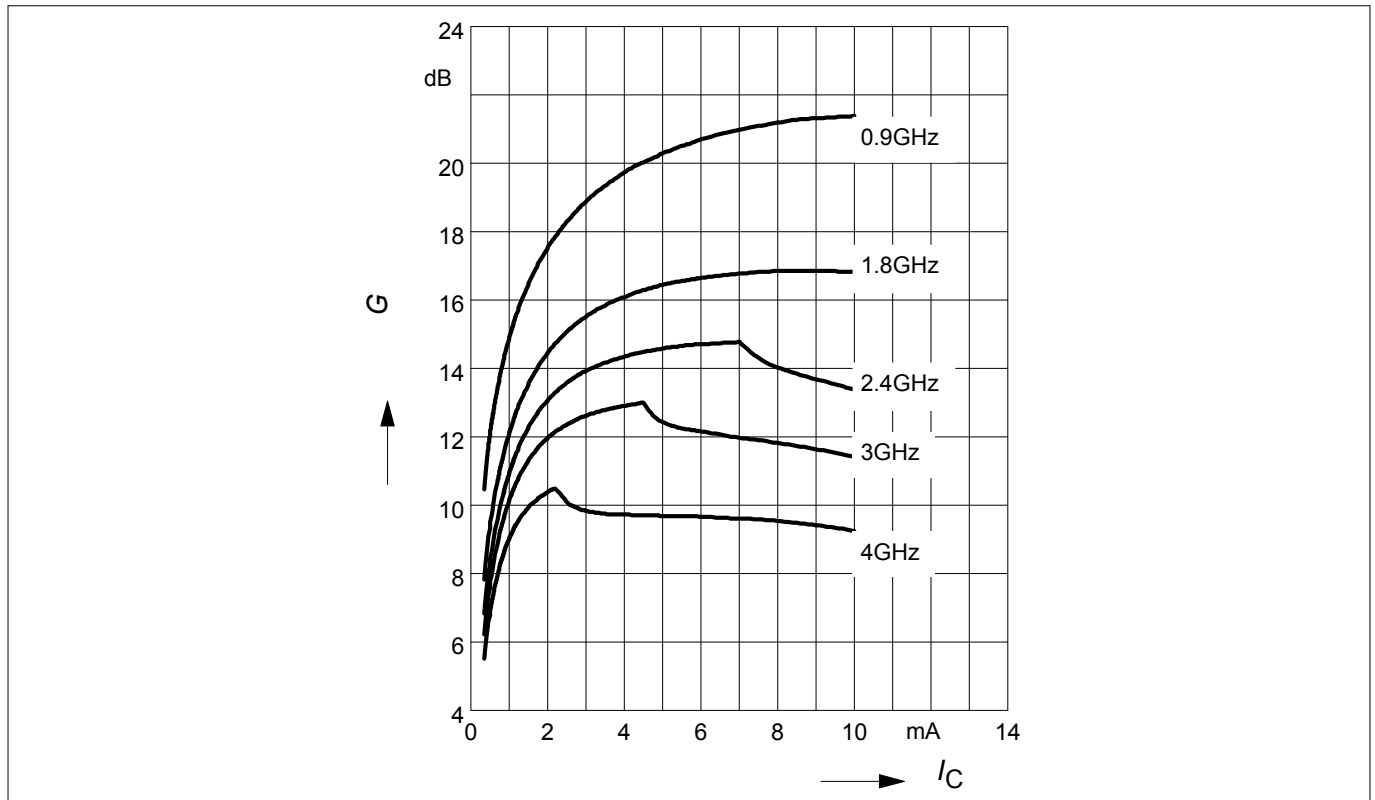


Figure 9 Maximum power gain $G_{\max} = f(I_C)$, $V_{CE} = 3\text{ V}$, $f = \text{parameter}$

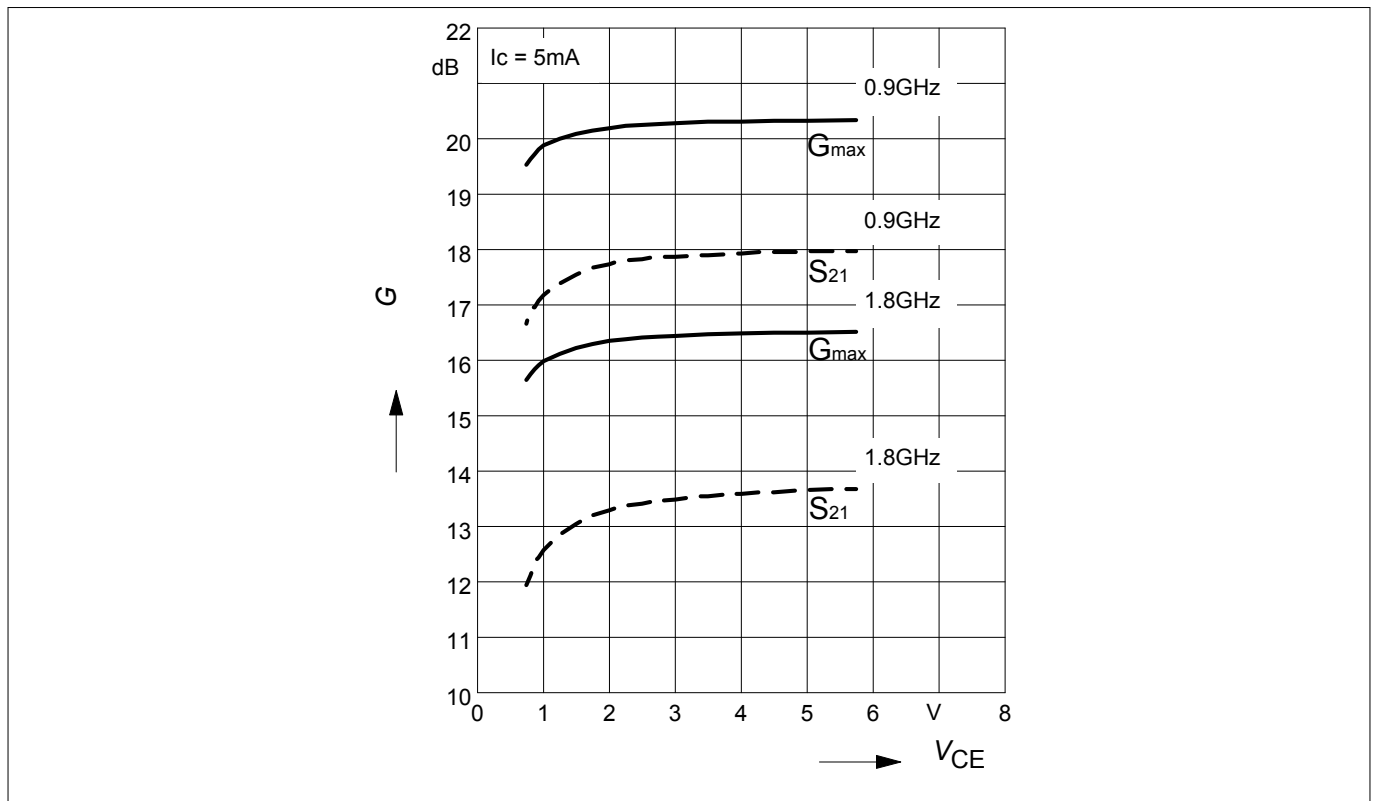


Figure 10 Maximum power gain $G_{\max} = f(V_{CE})$, transducer gain $IS_{21}I^2 = f(V_{CE})$, $I_C = 5\text{ mA}$, $f = \text{parameter in GHz}$

Electrical characteristics

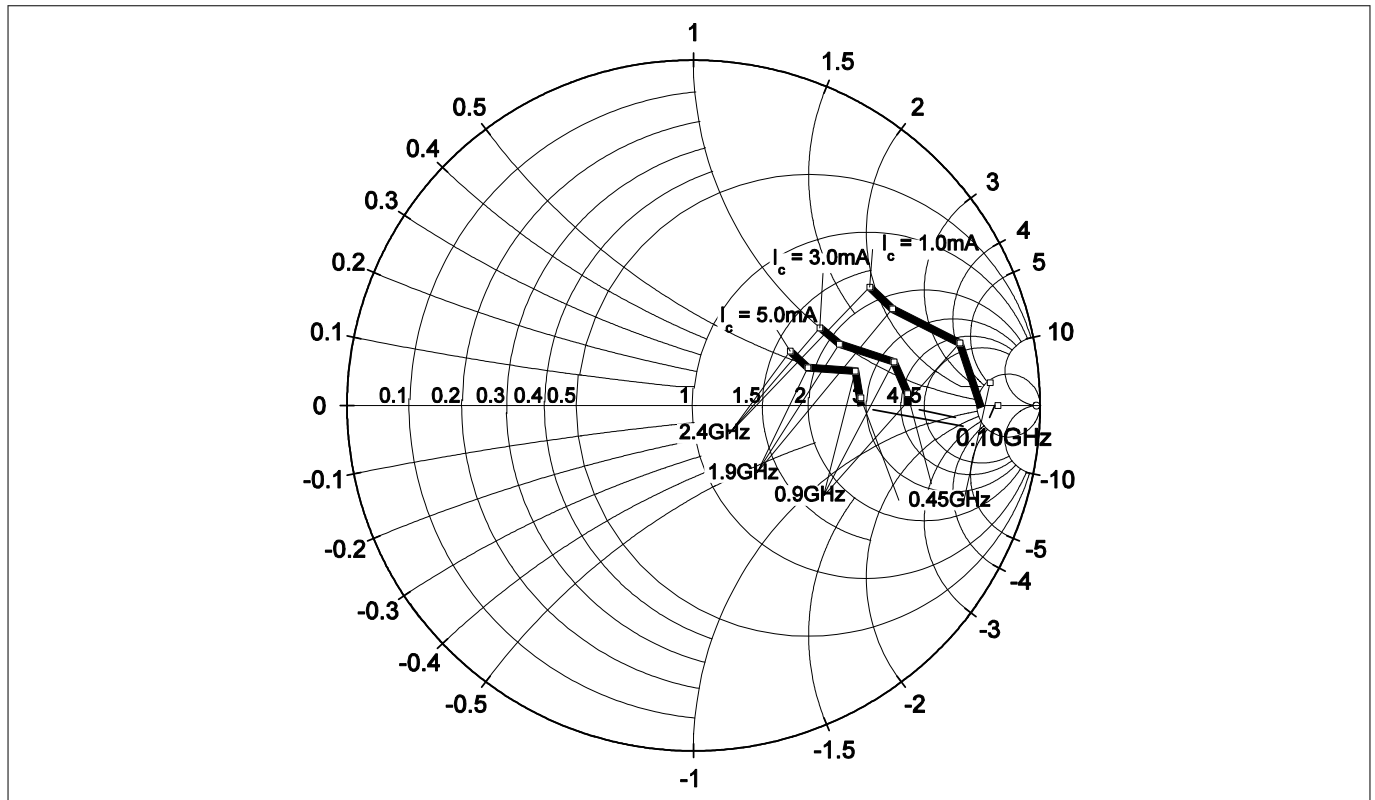


Figure 11 Source impedance for minimum noise figure $Z_{S,opt} = f(f)$, $V_{CE} = 1.5$ V, $I_C = \text{parameter}$

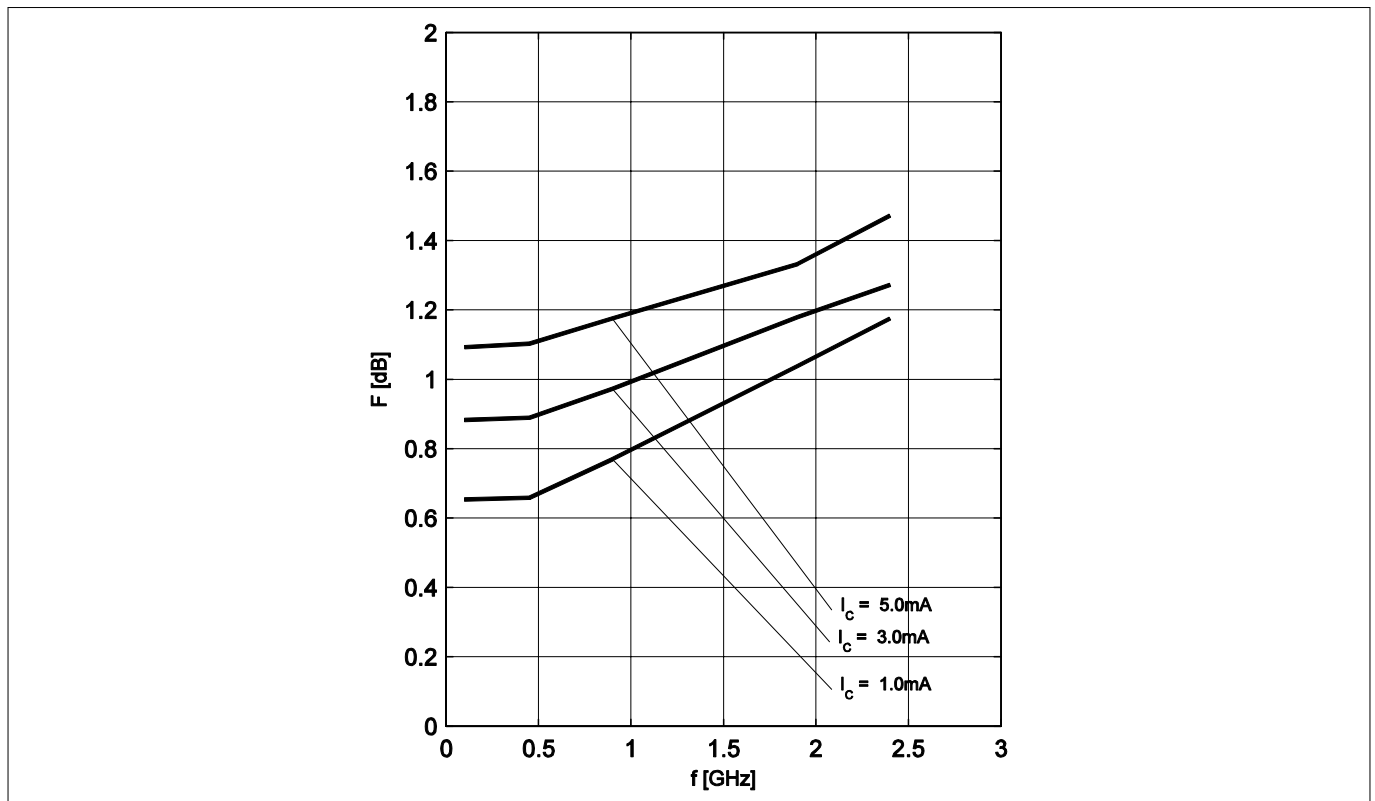


Figure 12 Noise figure $NF_{min} = f(f)$, $V_{CE} = 1.5$ V, $Z_S = Z_{S,opt}$, $I_C = 1 / 3 / 5$ mA

Electrical characteristics

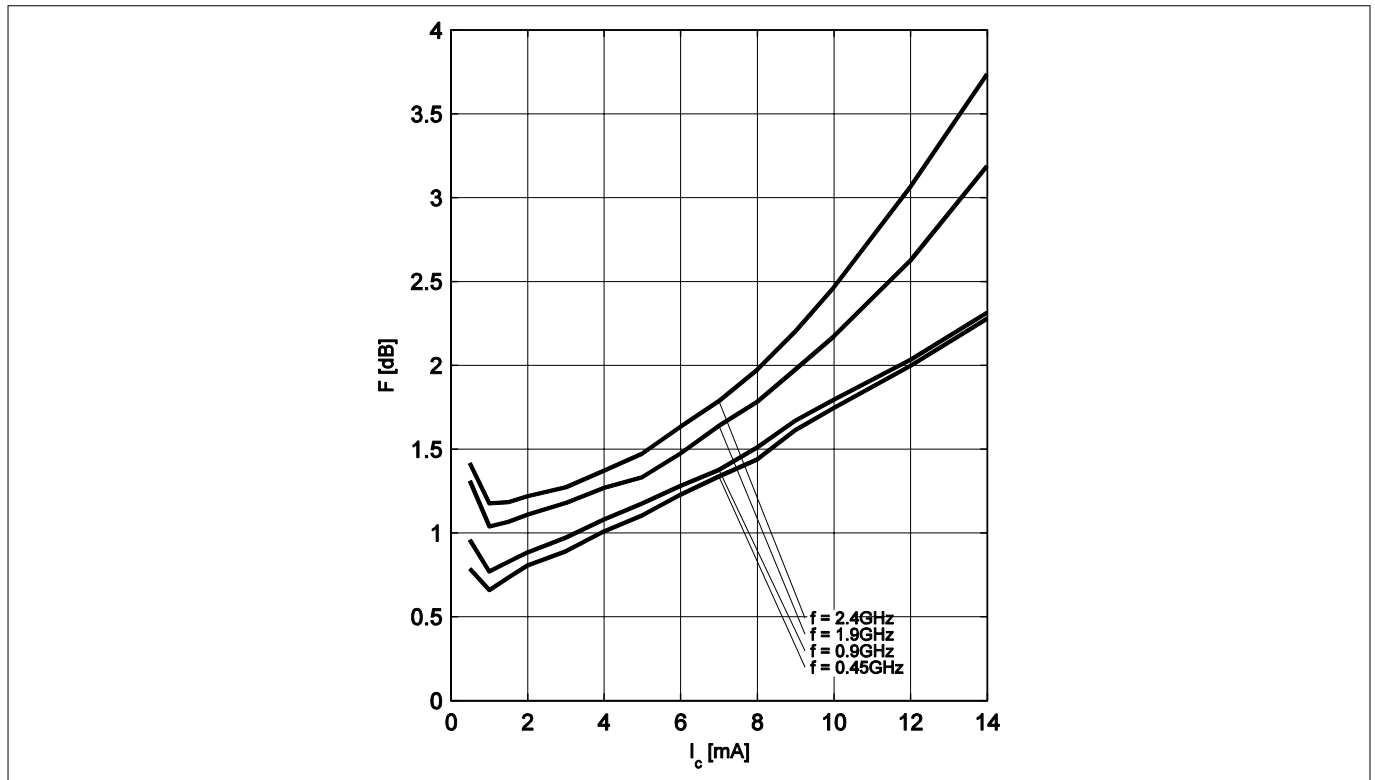


Figure 13 Noise figure $NF_{\min} = f(I_c)$, $V_{CE} = 1.5\text{ V}$, $Z_S = Z_{S,\text{opt}}$, $f = \text{parameter in GHz}$

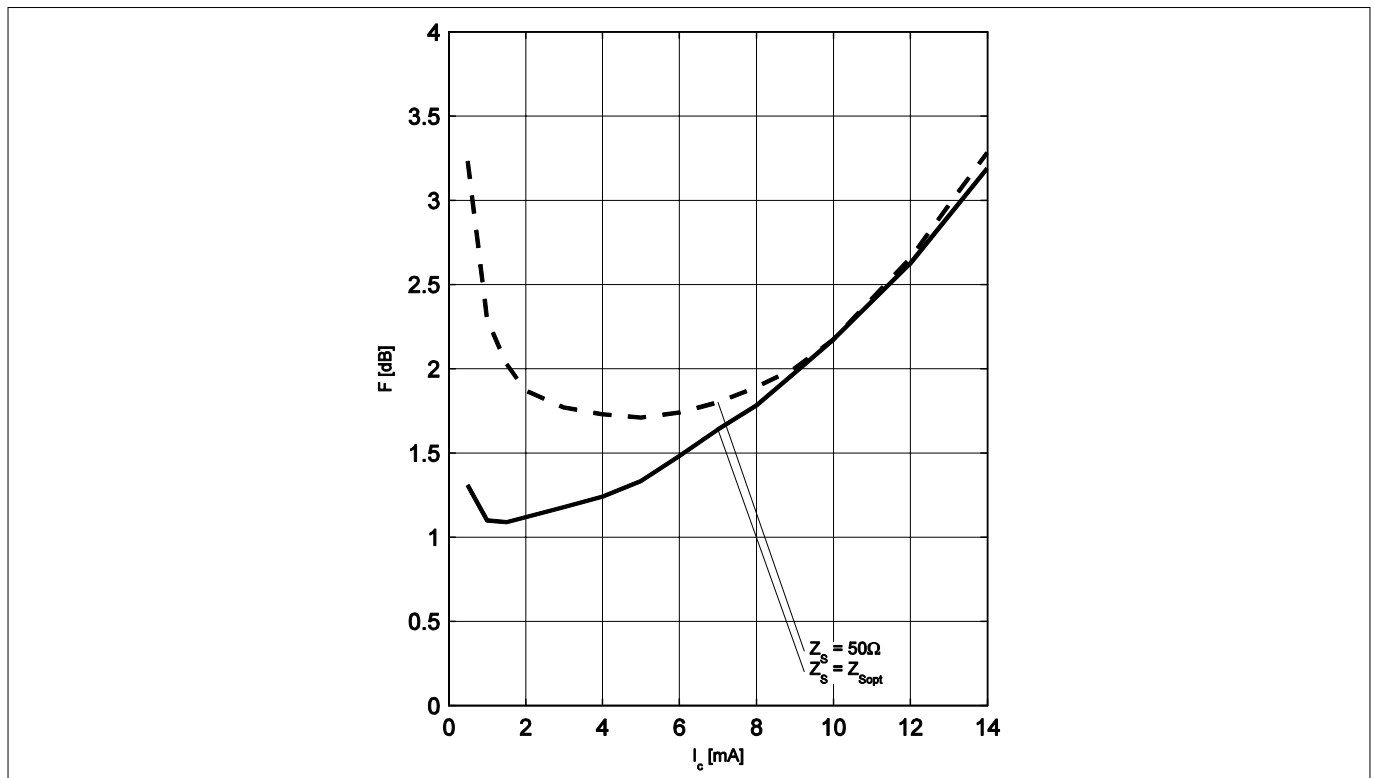


Figure 14 Noise figure $NF_{\min} = f(I_c)$, $Z_S = Z_{S,\text{opt}}$, $NF_{50} = f(I_c)$, $Z_S = 50\Omega$, $V_{CE} = 3\text{ V}$, $f = 1.9\text{ GHz}$

Note: The curves shown in this chapter have been generated using typical devices but shall not be considered as a guarantee that all devices have identical characteristic curves. $T_A = 25\text{ }^\circ\text{C}$.

BFR340F

Low profile silicon NPN RF bipolar transistor

Package information TSFP-3-1

4 Package information TSFP-3-1

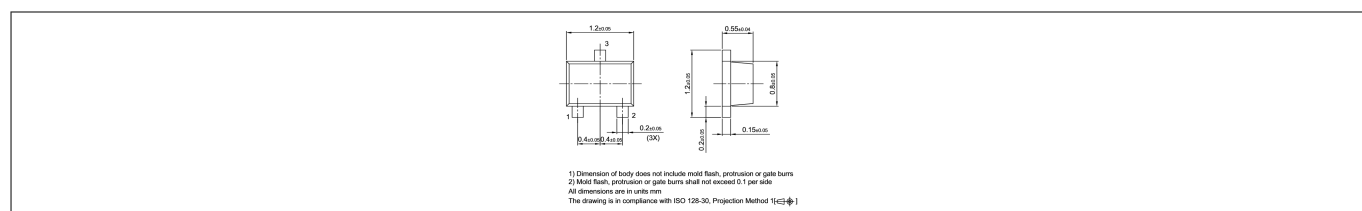


Figure 15 Package outline

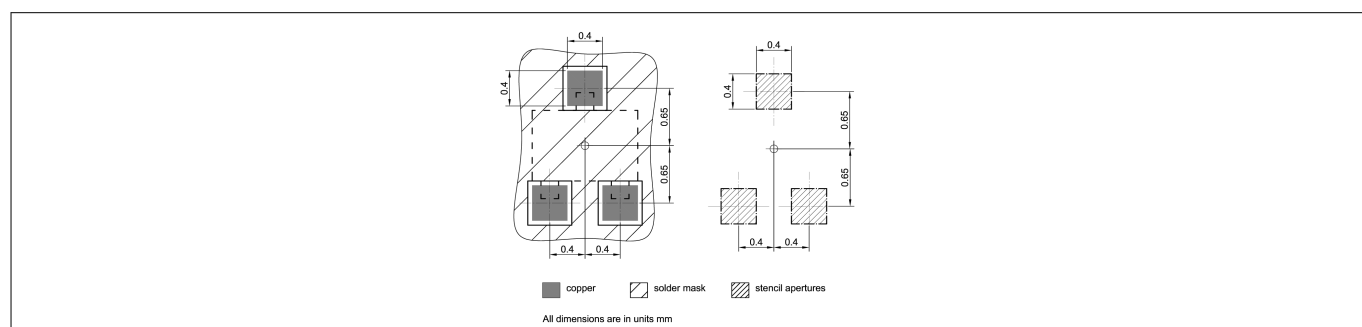


Figure 16 Foot print

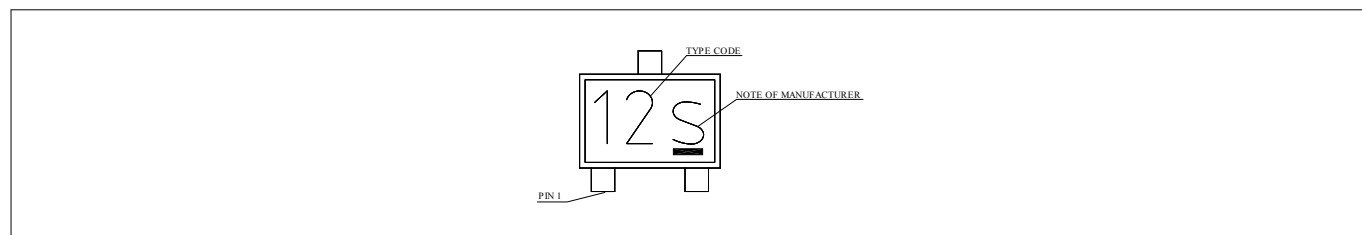


Figure 17 Marking layout example

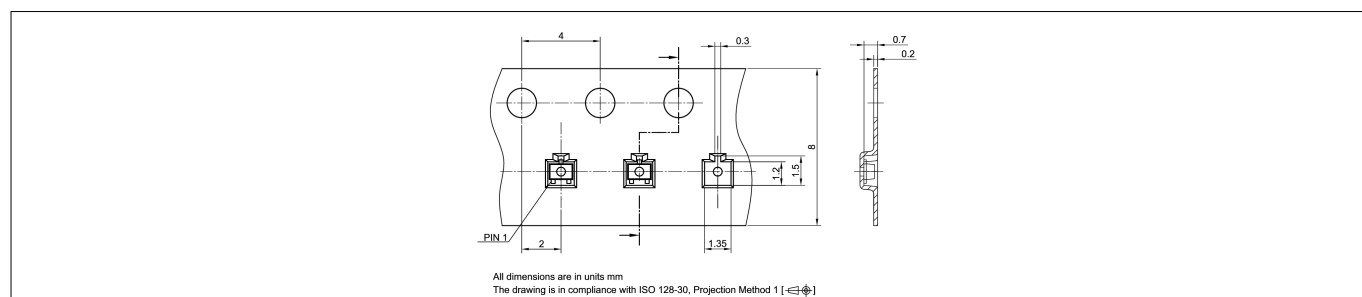


Figure 18 Tape information

Revision history

Revision history

Document version	Date of release	Description of changes
Revision 2.0	2019-01-25	New datasheet layout.

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Edition 2019-01-25

Published by
Infineon Technologies AG
81726 Munich, Germany

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Document reference
IFX-pky1525443005897

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